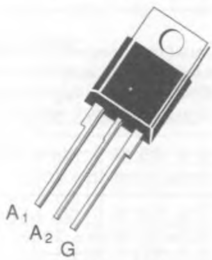
LOGIC LEVEL TRIACS

- I_{TRMS} = 6 A at T_c = 80 °C.
- V_{DRM} : 200 V to 800 V.
- I_{GT} = 5 mA (QI-II-III).
- $(di/dt)_c$ = 2.7 A / ms @ $(dv/dt)_c$ = 20 V / µs.
- SUITED FOR LOW POWER TRIGGER CIRCUITS (INTEGRATED CIRCUITS AND MICROPROCESSORS).
- GLASS PASSIVATED CHIP.
- HIGH EFFICIENCY SWITCHING.
- AVAILABLE IN INSULATED VERSION → BTA SERIES (INSULATING VOLTAGE : 2500 V_{RMS}) OR IN UNINSULATED VERSION → BTB SERIES.
- UL RECOGNIZED FOR BTA SERIES (E81734).

DESCRIPTION

New range suited for applications such as phase control and static switching on inductive or resistive load.



TO 220 AB
(CB-415 Plastic)

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
I_{TRMS}	RMS on-state current (360 ° conduction angle)	T_c = 80 °C	6	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25 C)	t = 8.3 ms	95	A
		t = 10 ms	85	
I^2t	I^2t value	t = 10 ms	36	A^2s
di/dt	Critical rate of rise of on-state current (1)	Repetitive F = 50 Hz	20	A /µs
		Non Repetitive	100	
T_{stg} T_j	Storage and operating junction temperature range		- 40, + 150 - 40, + 110	°C °C

Symbol	Parameter	BTA/BTB 06-					Unit
		200 TW	400 TW	600 TW	700 TW	800 TW	
V_{DRM}	Repetitive peak off-state voltage (2)	± 200	± 400	± 600	± 700	± 800	V

(1) Gate supply : I_G = 50 mA – dI_G/dt = 1 A / µs.
(2) T_j = 110 °C.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th (j-a)}$	Junction to ambient	60	°C/W
$R_{th (j-c)}$ DC	Junction to case for DC	4.8	°C/W
$R_{th (j-c)}$ AC	Junction to case for 360 ° conduction angle (F = 50 Hz)	3.6	°C/W

GATE CHARACTERISTICS (maximum values)

P_{GM} = 40 W (t = 10 µs) $P_{G (AV)}$ = 1 W I_{GM} = 4 A (t = 10 µs) V_{GM} = 16 V (t = 10 µs).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions	Quadrants	Min.	Typ.	Max.	Unit
I_{GT}	T_j = 25 °C V_D = 12 V R_L = 33 Ω Pulse duration > 20 µs	I-II-III			5	mA
V_{GT}	T_j = 25 °C V_D = 12 V R_L = 33 Ω Pulse duration > 20 µs	I-II-III			1.5	V
V_{GD}	T_j = 110 °C V_D = V_{DRM} R_L = 3.3 kΩ Pulse duration > 20 µs	I-II-III	0.2			V
I_H*	T_j = 25 °C I_T = 100 mA Gate open R_L = 140 Ω				15	mA
I_L	T_j = 25 °C V_D = 12 V R_L = 33 Ω Pulse duration > 20 µs I_G = 25 mA	I-III		15		mA
		II		30		
V_{TM}*	T_j = 25 °C I_{TM} = 8.5 A t_p = 10 ms				1.75	V
I_{DRM}*	T_j = 25 °C V_{DRM} rated Gate open				10	µA
	T_j = 110 °C				500	
dv/dt*	T_j = 110 °C Gate open Linear slope up to 0.67 V_{DRM}		20			V/µs
$(di/dt)_c$*	T_j = 110 °C $(dv/dt)_c$ = 0.1 V/µs		2.7	4		A/ms
	T_j = 110 °C $(dv/dt)_c$ = 20 V/µs		1.3	2.7		
t_{gt}	T_j = 25 °C di_G/dt = 1 A/µs I_G = 25 mA I_T = 8.5 A V_D = V_{DRM}	I-II-III		2		µs

* For either polarity of electrode A_2 voltage with reference to electrode A_1.

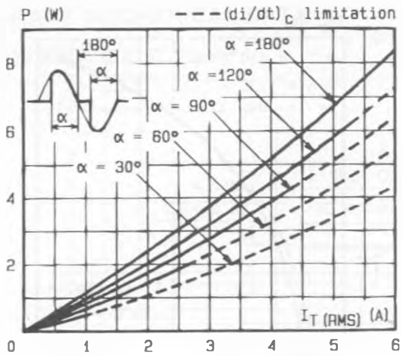


Fig.1 - Maximum mean power dissipation versus RMS on-state current (F = 60 Hz).

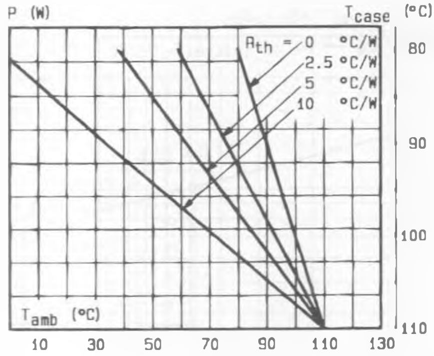


Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

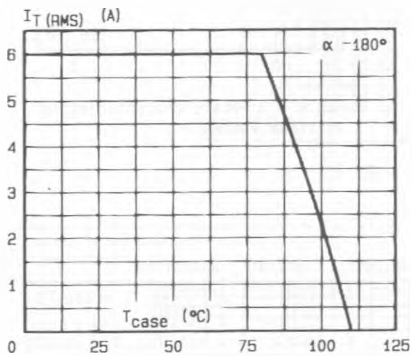


Fig.3 - RMS on-state current versus case temperature.

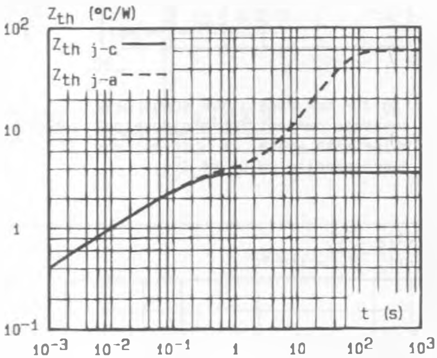


Fig.4 - Thermal transient impedance junction to case and junction to ambient versus pulse duration.

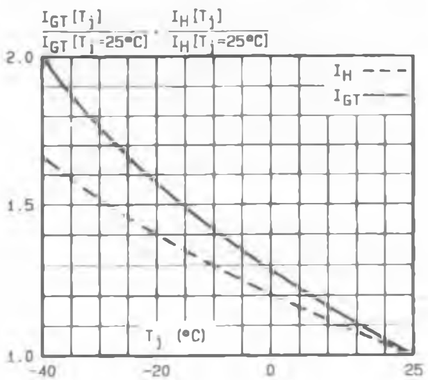


Fig.5 - Relative variation of gate trigger current and holding current versus junction temperature.

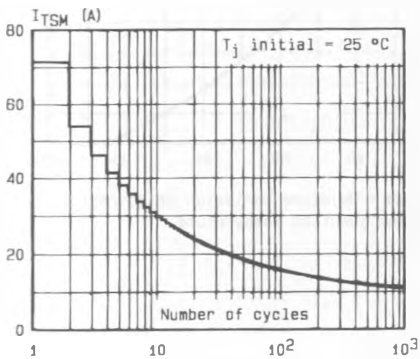


Fig.6 - Non repetitive surge peak on-state current versus number of cycles.

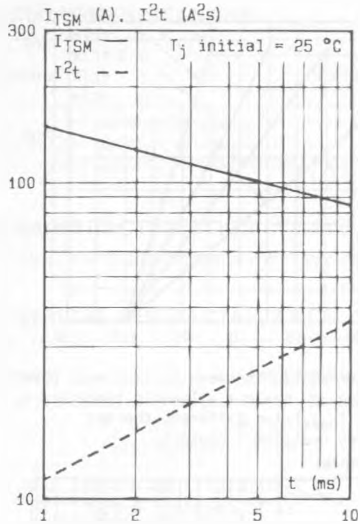


Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leqslant 10$ ms, and corresponding value of I^2t.

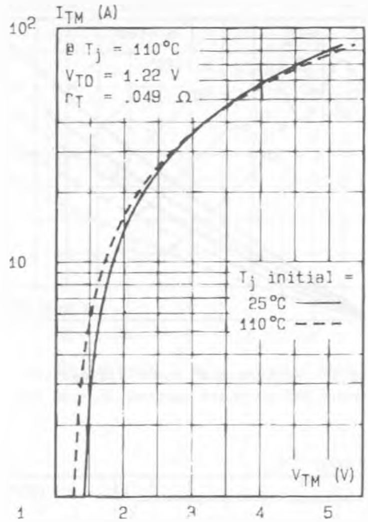


Fig.8 - On-state characteristics (maximum values).

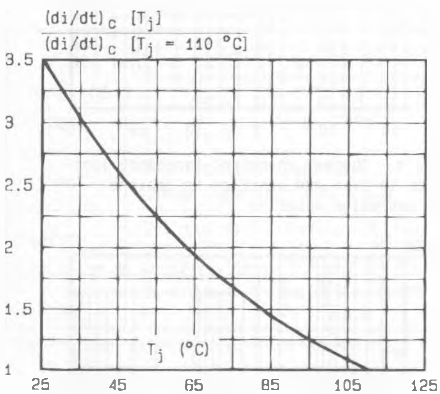


Fig.9 - Relative variation of $(di/dt)_c$ versus junction temperature.

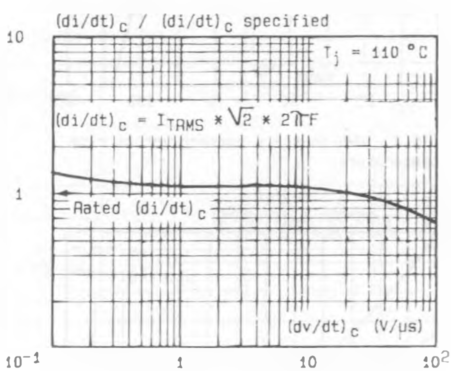


Fig.10 - Relative variation of $(di/dt)_c$ versus $(dv/dt)_c$ (inductive load) (typical values).